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The Flat-Plate Solar Array Project is sponsored by the U.S. Department of Energy and forms part of the Solar Photovoltaic Conversion Program to initiate a major effort toward the development of low-cost solar arrays. This work was performed for the Jet Propulsion Laboratory, California Institute of Technology by agreement between NASA and DOE.

ABSTRACT/SUMMARY

Various Mo/Sn screen printing pastes were scheduled for evaluation. Cells are first prefired in air and then fired in a H₂ atmosphere. Preliminary results are encouraging.

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Section 1.0

INTRODUCTION

The objective of this contract is the optimization, evaluation, and demonstration of a novel metallization applied by a screen printing process. The process will be evaluated on both CZ and non-CZ silicon wafers.

Section 2.0

TECHNICAL DISCUSSION

2.1 PASTE FORMULATION

Five screen printing pastes have been prepared by Thick Film Systems, Inc. The pastes are 80-85% solids using vehicle #3347. The metal content in parts by weight follows:

Type	TFS #	Sylvania 280-325 Mo	Atlantic Equipment Engineers SN 266 Sn	Ferro Plant PX-41 TiH
A	DP-E570	19.5	80.0	0.5
B	DP-E571	50.0	49.5	0.5
C	DP-E572	70.0	29.5	0.5
D	DP-E573	49.0	49.0	2.0
E	DP-E574	48.0	48.0	4.0

2.2 CELL MANUFACTURE

The process for cell manufacture was fixed at the start of the program up to the front printing step. Figure 1 shows the traveler that was used.

Wafers were bought from Smiel. The wafers are 3.0" round, 15 mils thick, 7-14 Ω -cm, 1-0-0, Type P silicon.

Cell preparation begins with a 30% NaOH etch followed by phosphine diffusion. Al paste is then screen printed on the back and fired

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CELL MANUFACTURING

PRODUCTION LOT NO: _____

START DATE: _____

Silicon

Manf -	Resist -
Type -	PO #
Orient -	Size -
Thickness -	Series # -

OPERATION	DATE	OPERATOR	NO. OF CELLS			REASON FOR REJECTION	
			START	GOOD	BAD		
SURFACE PREPARATION							
DIFFUSE							
PRINT AL BACK							
FIRE AL BACK							
CLEAN BACK							
LASER SCRIBE							
PRINT							Screen - Paste -
PREFIRE							Furnace - Gas -
PREFIRE							Furnace - Gas -
FIRE							Furnace - Gas -
FIRE							Furnace - Gas -
FIRE							Furnace - Gas
FIRE							Furnace - Gas -
TEST							
AR COAT							
TEST							

Figure 1

CELL TRAVELER FOR METALLIZATION PROGRAM

to form the P+ layer. The backs are cleaned and a 2.1" x 2.1" square wafer is laser-scribed out of the round wafer. These squares are then ready for front metallization printing.

2.3 PASTE EVALUATION

Type A paste was used exclusively for the initial evaluations. Procurement problems forced the use of a round front metallization pattern on a square wafer. This pattern led to high series resistance. Screen printed silver cells were used as controls. The IV curve for the best silver cell is shown in Figure 2. This cell has no AR coating. The shunt resistance was measured at 0.5V reverse and found to be 25.0Ω.

The first parameters used for evaluation were a prefire in an IR belt furnace followed by firing in a 5% H₂/95% N₂ atmosphere. Cells were prefired at 500°C at various belt speeds and then fired for 3 minutes in the reducing atmosphere for 30 minutes. The cells showed poor IV curve caused by shunting and high series resistance.

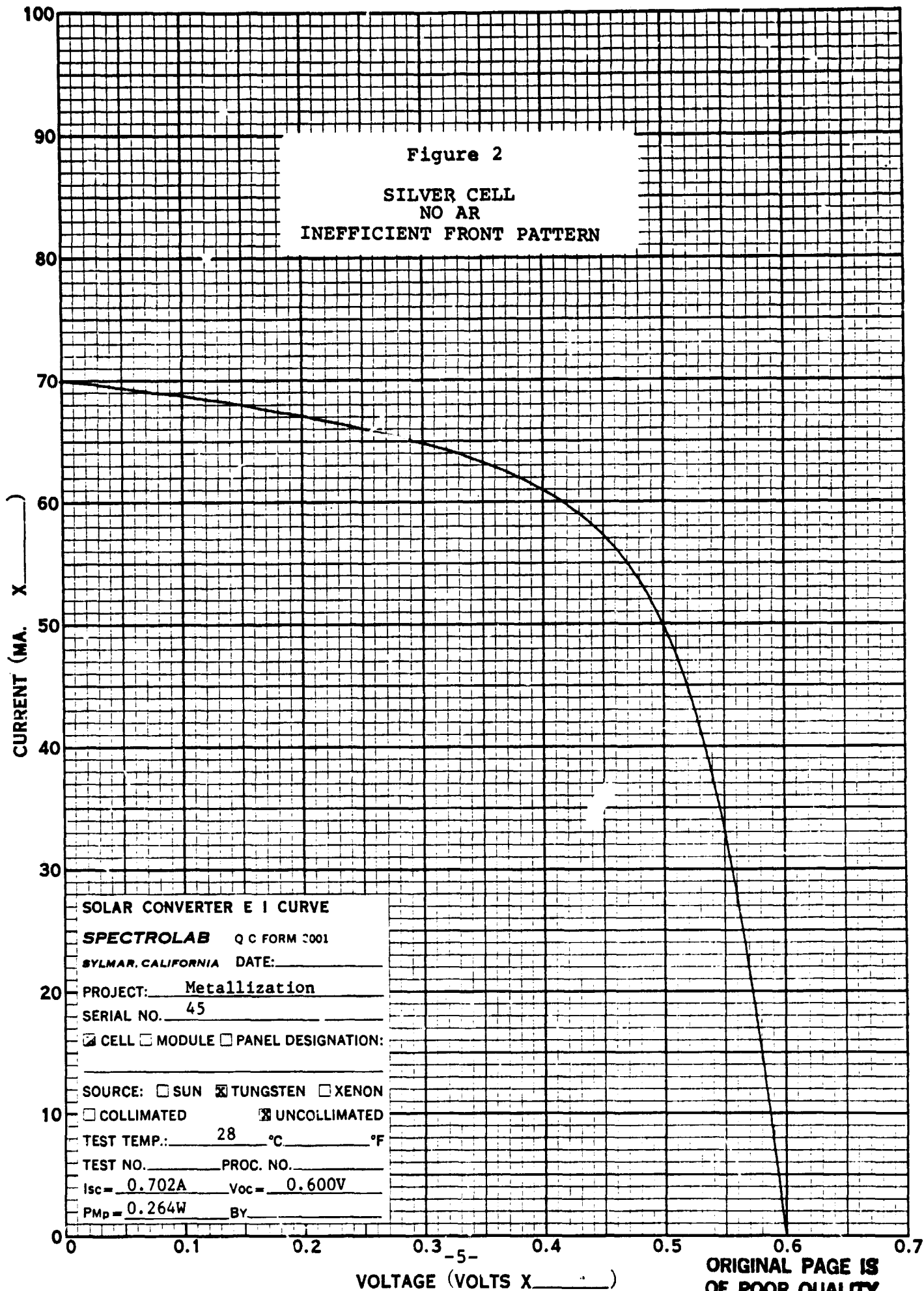
A second experiment tried 450° and 500° prefires followed by shorter firing times and 650°C. These cells were also poor.

Next, firing was tried in a 100% H₂ atmosphere. Cells showed metallic-like contacts similar to silver contacts. Curve shape improved.

The next experiment followed the matrix shown in Table 1.

The best cells are those fired at 575° for 1 minute. Prefiring at 18"/minute seems slightly better than 9"/minute. Figures 3 and 4 are IV curves of the best two cells. Table 2 shows the

Figure 2
SILVER CELL
NO AR
INEFFICIENT FRONT PATTERN



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Table 1

Prefire	18"/min. 500°	9"/min. 500°	
Fire	30 secs.	30 secs.	
	1 min.	1 min.	} 600°
	2 min.	2 min.	
	5 min.	5 min.	
	1 min.	1 min.	575°
	1 min.	1 min.	550°
	1 min.	1 min.	525°

Figure 3
MOLY/TIN CELL
NO AR
INEFFICIENT FRONT PATTERN

CURRENT (MA. X)

SOLAR CONVERTER E I CURVE

SPECTROLAB Q C FORM 3001

SYLMAR, CALIFORNIA DATE:

PROJECT: Metallization

SERIAL NO. 13

☒ CELL ☐ MODULE ☐ PANEL DESIGNATION:

SOURCE: ☐ SUN ☒ TUNGSTEN ☐ XENON

☐ COLLIMATED ☒ UNCOLLIMATED

TEST TEMP.: 28 °C °F

TEST NO. PROC. NO.

Isc = 0.680A Voc = 0.593V

Pmp = 0.231W By

VOLTAGE (VOLTS X 1)

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Figure 4
MOLY TIN CELL
NO AR
INEFFICIENT FRONT PATTERN

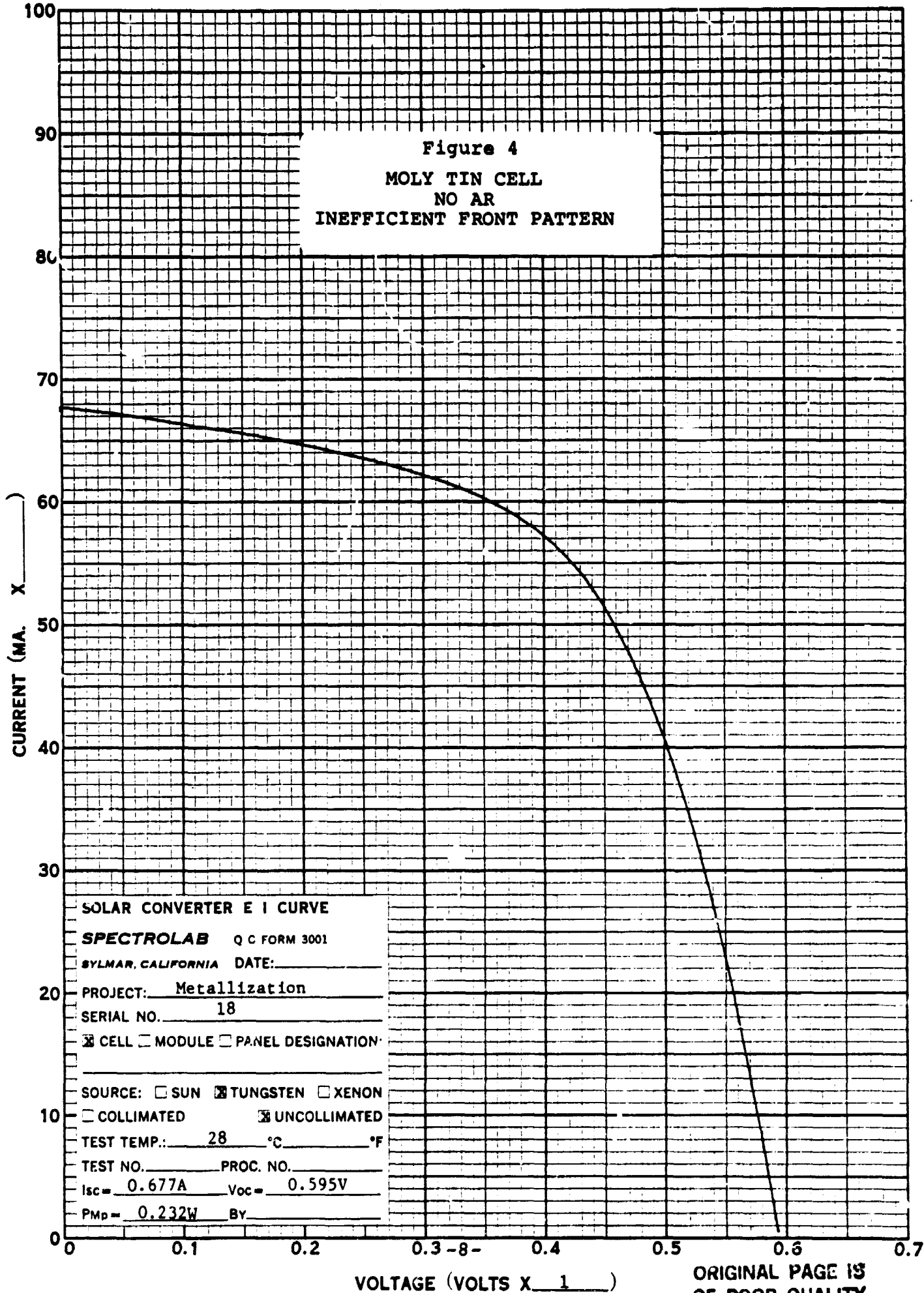


Table 2
SUMMARY OF CELL CHARACTERISTICS

<u>Cell #</u>	<u>I_{sc}</u>	<u>V_{oc}</u>	<u>I₅₀₀</u>	<u>I_{mp}</u>	<u>V_{mp}</u>	<u>P</u>	<u>FF</u>	<u>E</u>	<u>(If AR)</u>	<u>R_{shunt}</u>
13 (Mo/Sn)	680	593	409	541	427	.231	.573	8.12	(10.7)	39.7
18 (Mo/Sn)	677	595	411	543	428	.232	.576	8.15	(10.8)	61.7
45 (Ag)	702	600	501	579	463	.264	.627	9.28	(12.3)	25.0

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characteristics of these cells compared to the silver controls. The cells have not been AR coated and the AR efficiencies are based on a 32% gain.

The shunt resistance of the Mo/Sn cells is higher than that of silver. This indicates it may be possible to make Mo/Sn metallized cells that are superior to AG cells, if the series resistance problems are overcome.

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Section 3.0

CONCLUSIONS AND RECOMMENDATIONS

There are no conclusions or recommendations for this period.

Section 4.0

ACTIVITIES PROJECTION

More cells will be fabricated using the Type A paste. Other pastes will be evaluated. Interconnection tests will be run to determine metallization adherence. A milestone and delivery schedule follows.

